# 80 V NPN, 10 A Power Transistor

These series of plastic, silicon NPN power transistors can be used as general purpose power amplification and switching such as output or driver stages in applications such as switching regulators, converters and power amplifiers.

#### **Features**

- Fast Switching Speeds
- High Frequency
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

#### **Benefits**

- Reliable Performance at Higher Powers
- Symmetrical Characteristics in Complementary Configurations
- Accurate Reproduction of Input Signal
- Greater Dynamic Range
- High Amplifier Bandwidth

#### **Applications**

- High-end Consumer Audio Products
  - Home Amplifiers
  - Home Receivers

#### **MAXIMUM RATINGS** $(T_A = 25^{\circ}C)$

Rating	Symbol	Max	Unit
Collector-Emitter Voltage	V <sub>CEO</sub>	80	Vdc
Emitter-Base Voltage	V <sub>EBO</sub>	5.0	Vdc
Collector Current - Continuous	Ic	10	Α
Collector Current - Peak (Note 1)	I <sub>CM</sub>	20	Α
Total Power Dissipation @ T <sub>C</sub> = 25°C	$P_{D}$	120	Watts

#### THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{ heta JC}$	1.04	°C/W
Junction and Storage Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	-65 to +150	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. Pulse Test: Pulse Width = 5 ms, Duty Cycle  $\leq$  10%.

\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

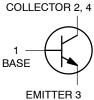


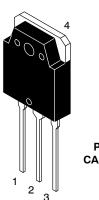
#### ON Semiconductor®

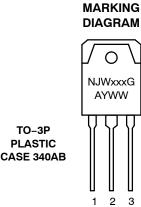
http://onsemi.com

## 80 VOLT, 10 AMPS NPN POWER TRANSISTORS

### NPN







3 I 1

xxx = TBD

G = Pb-Free Package
A = Assembly Location

YearWork Week

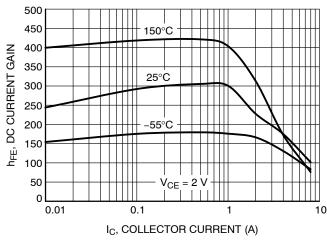
#### **ORDERING INFORMATION**

Device	Package	Shipping
NJW44H11G	TO-3P (Pb-Free)	30 Units/Rail

#### **ELECTRICAL CHARACTERISTICS** (T<sub>A</sub> = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS			•		
Collector–Emitter Sustaining Voltage ( $I_C = 30 \text{ mAdc}, I_B = 0$ )	V <sub>CEO</sub>	80	_	_	Vdc
Collector–Cutoff Current $(V_{CE} = Rated V_{CEO}, V_{BE} = 0)$	I <sub>CES</sub>	-	-	10	μAdc
Emitter Cutoff Current (V <sub>BE</sub> = 5.0 Vdc)	I <sub>EBO</sub>	-	_	10	μAdc
ON CHARACTERISTICS			•	•	•
DC Current Gain $ (I_C = 2 \text{ A, } V_{CE} = 2 \text{ V}) $ $ (I_C = 4 \text{ A, } V_{CE} = 2 \text{ V}) $	h <sub>FE</sub>	100 80	- -	400 320	-
Collector-Emitter Saturation Voltage (I <sub>C</sub> = 8 A, I <sub>B</sub> = 400 mA)	V <sub>CE(sat)</sub>	-	-	1.0	V
Base-Emitter Turn-on Voltage (I <sub>C</sub> = 8 A, V <sub>CE</sub> = 2.0 V)	V <sub>BE(on)</sub>	-	-	1.5	V
DYNAMIC CHARACTERISTICS	<u>-</u>		-		=
Output Capacitance (V <sub>CB</sub> = 10 V, f = 1.0 MHz)	C <sub>obo</sub>	-	65	-	pF
Cutoff Frequency ( $I_C = 500 \text{ mA}$ , $V_{CE} = 5 \text{ V}$ , $f = 1.0 \text{ MHz}$ )	f⊤	-	85	-	MHz
SWITCHING TIMES	<u>.</u>	•	•	•	•
Delay and Rise Times (I <sub>C</sub> = 5.0 Adc, I <sub>B1</sub> = 0.5 A)	$t_d + t_r$	-	300	-	ns
Storage Time $(I_C = 5.0 \text{ Adc}, I_{B1} = I_{B2} = 0.5 \text{ A})$	t <sub>s</sub>	-	500	-	ns
Fall Time $(I_C = 5.0 \text{ Adc}, I_{B1} = I_{B2} = 0.5 \text{ A})$	t <sub>f</sub>	-	140	-	ns

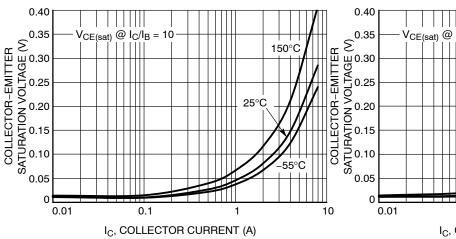
#### **TYPICAL CHARACTERISTICS**



500 450 150°C 400 hFE, DC CURRENT GAIN 350 25°C 300 250 200 -55°C 150 100 50 0 0.01 10 IC, COLLECTOR CURRENT (A)

Figure 1. DC Current Gain

Figure 2. DC Current Gain



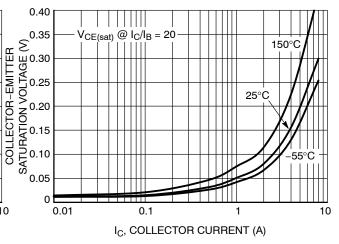
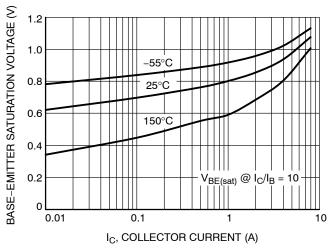


Figure 3. Collector Emitter Saturation Voltage

Figure 4. Collector Emitter Saturation Voltage



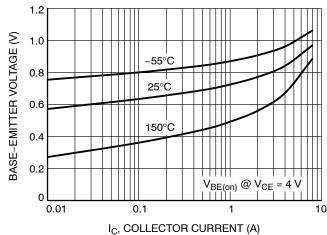
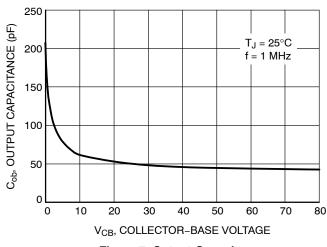


Figure 5. Base Emitter Saturation Voltage

Figure 6. Base Emitter "ON" Voltage

#### **TYPICAL CHARACTERISTICS**



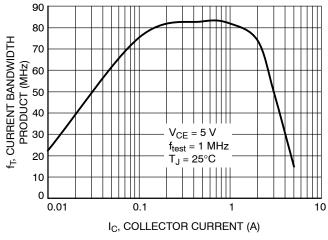
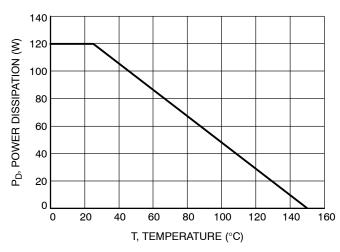
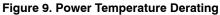


Figure 7. Output Capacitance

Figure 8. Current Gain Bandwidth Product





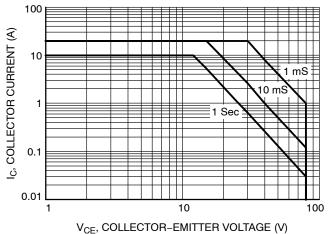
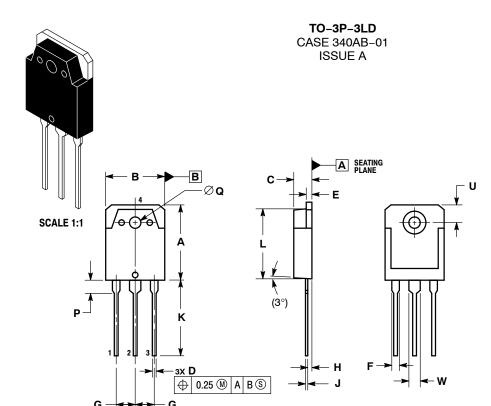


Figure 10. Safe Operating Area (SOA)

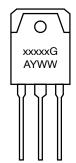
**DATE 30 OCT 2007** 



- IOIES:
  1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
  2. CONTROLLING DIMENSION: MILLIMETERS
  3. DIMENSION & APPLIES TO PLATED TERMINAL AND IS MEASURED BETWEEN 0.15 AND 0.30mm FROM THE TERMINAL TIP.
- DIMENSION A AND B DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

	MILLIMETERS		
DIM	MIN	NOM	MAX
Α	19.70	19.90	20.10
В	15.40	15.60	15.80
С	4.60	4.80	5.00
D	0.80	1.00	1.20
Е	1.45	1.50	1.65
F	1.80	2.00	2.20
G	5.45 BSC		
Н	1.20	1.40	1.60
J	0.55	0.60	0.75
K	19.80	20.00	20.20
L	18.50	18.70	18.90
Р	3.30	3.50	3.70
Q	3.10	3.20	3.50
C	5.00 REF		
A	2 80	3 00	3 20

#### **GENERIC MARKING DIAGRAM\***



XXXXX = Specific Device Code = Pb-Free Package G = Assembly Location Α = Year

WW = Work Week

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G", may or not be present.

#### PIN 1. BASE 2. COLLECTOR EMITTER COLLECTOR

STYLE 1:

STYLE 2: ANODE CATHODE 2.

STYLE 3: PIN 1. GATE 2. DRAIN

ANODE SOURCE CATHODE DRAIN

Υ

DOCUMENT NUMBER:	98AON25095D	Electronic versions are uncontrolled except when accessed directly from the Document Repositor Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.		
DESCRIPTION:	TO-3P-3LD		PAGE 1 OF 1	

ON Semiconductor and (III) are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. ON Semiconductor does not convey any license under its patent rights nor the rights of others.

onsemi, Onsemi, and other names, marks, and brands are registered and/or common law trademarks of Semiconductor Components Industries, LLC dba "onsemi" or its affiliates and/or subsidiaries in the United States and/or other countries. onsemi owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of onsemi's product/patent coverage may be accessed at <a href="www.onsemi.com/site/pdf/Patent-Marking.pdf">www.onsemi.com/site/pdf/Patent-Marking.pdf</a>. Onsemi reserves the right to make changes at any time to any products or information herein, without notice. The information herein is provided "as-is" and onsemi makes no warranty, representation or guarantee regarding the accuracy of the information, product features, availability, functionality, or suitability of its products for any particular purpose, nor does onsemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using onsemi products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by onsemi. "Typical" parameters which may be provided in onsemi data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. onsemi does not convey any license under any of its intellectual property rights nor the rights of others. onsemi products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA class 3 medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase

#### ADDITIONAL INFORMATION

**TECHNICAL PUBLICATIONS:** 

 $\textbf{Technical Library:} \ \underline{www.onsemi.com/design/resources/technical-documentation}$ 

onsemi Website: www.onsemi.com

ONLINE SUPPORT: www.onsemi.com/support

For additional information, please contact your local Sales Representative at

www.onsemi.com/support/sales